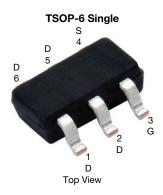


Automotive P-Channel 60 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY					
V _{DS} (V)	-60				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.095				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.135				
I _D (A)	-5.3				
Configuration	Single				
Package	TSOP-6				

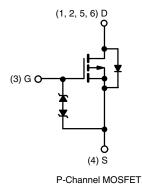
Marking Code: 8Y

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified c
- 100 % R_q and UIS tested
- Typical ESD protection 800 V
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



FREE



ORDERING INFORMATION	
Package	TSOP-6
Lead (Pb)-free and halogen-free	SQ3427AEEV (for detailed order number please see www.vishay.com/doc?79771)

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	V _{DS}	-60	V			
Gate-Source Voltage	V _{GS}	± 20	V			
Continuous Drain Current	T _C = 25 °C		-5.3			
Continuous Drain Current	T _C = 125 °C	l _D	-3			
Continuous Source Current (Diode Conduction)	I _S	-6.3	А			
Pulsed Drain Current ^a		I _{DM}	-21			
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	-21			
Single Pulse Avalanche Energy	L=0.1 mm	E _{AS}	22	mJ		
Maximum Power Dissipation ^a	T _C = 25 °C	D	5	W		
	T _C = 125 °C	P_D	1.6	VV		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount b	R_{thJA}	110	°C/W	
Junction-to-Foot (Drain)		R_{thJF}	30	C/VV	

Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. When mounted on 1" square PCB (FR4 material)
- c. Parametric verification ongoing

S21-1246-Rev. B, 10-Jan-2022



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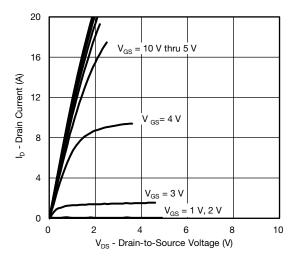
SPECIFICATIONS ($T_C = 25 ^{\circ}C$,	unless otherw	vise noted)						
PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static								
Drain-Source Breakdown Voltage	V _{DS}	V _{GS}	$V_{GS} = 0$, $I_D = -250 \mu A$		-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	V _{GS} , I _D = -250 μA	-1.5	-2	-2.5	7 °	
Octo Common Lockson	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 10	mA	
Gate-Source Leakage		V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 10 \text{ V}$		-	± 2		
		$V_{GS} = 0 V$	V _{DS} = -60 V	-	-	-1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = -60 V, T _J = 125 °C	-	-	-50	μA	
		V _{GS} = 0 V	V _{DS} = -60 V, T _J = 175 °C	-	-	-150		
On-State Drain Current a	I _{D(on)}	V _{GS} = -10 V	V _{DS} ≤ -5 V	-10	-	-	Α	
		V _{GS} = -10 V	I _D = -4.5 A	-	0.079	0.095		
Drain-Source On-State Resistance a		V _{GS} = -10 V	I _D = -4.5 A, T _J = 125 °C	-	-	0.148	Ω	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = -10 V	I _D = -4.5 A, T _J = 175 °C	-	-	0.178		
		V _{GS} = -4.5 V	I _D = -3.5 A	-	0.112	0.135		
Forward Transconductance ^a	9 _{fs}	$V_{DS} = -15 \text{ V}, I_D = -4 \text{ A}$		-	9	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}			-	700	1000		
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = -30 \text{ V}, f = 1 \text{ MHz}$	-	90	120	pF	
Reverse Transfer Capacitance	C _{rss}	1		-	50	75		
Total Gate Charge c	Qg			-	15.3	22		
Gate-Source Charge ^c	Q _{gs}	V _{GS} = -10 V	$V_{DS} = -30 \text{ V}, I_{D} = -5 \text{ A}$	-	2.5	-	nC	
Gate-Drain Charge c	Q _{gd}	1		-	5.4	-		
Gate Resistance	Rg	f = 1 MHz		2.7	5.4	8.1	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	8	12		
Rise Time ^c	t _r	V_{DD} = -30 V, R_L = 6 Ω $I_D \cong$ -5 A, V_{GEN} = -10 V, R_g = 1 Ω		-	24	35	ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	26	38		
Fall Time ^c	t _f			-	33	50		
Source-Drain Diode Ratings and Chara	cteristics b				•			
Pulsed Current ^a	I _{SM}			-	-	-21	Α	
Forward Voltage	V _{SD}	I _F = -1.6 A, V _{GS} = 0 V		-	-0.8	-1.2	V	

Notes

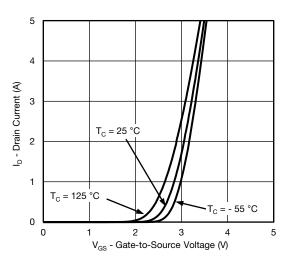
- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

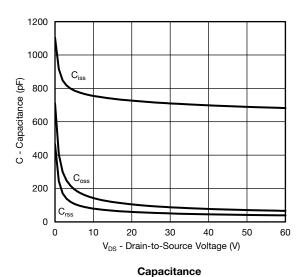


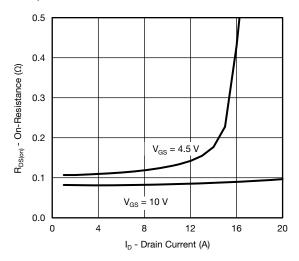


Output Characteristics

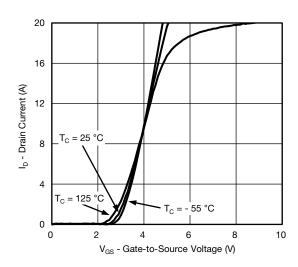


Transfer Characteristics

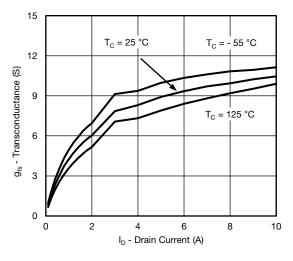




On-Resistance vs. Drain Current and Gate Voltage

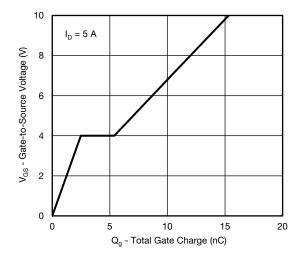


Transfer Characteristics

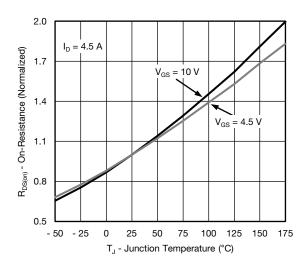


Transconductance

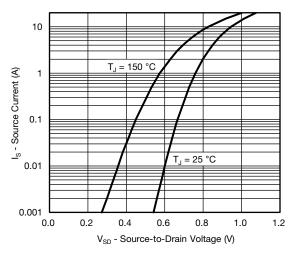




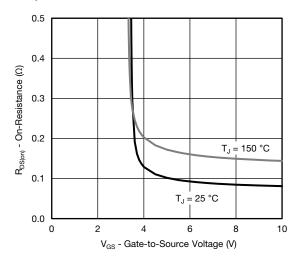
Gate Charge



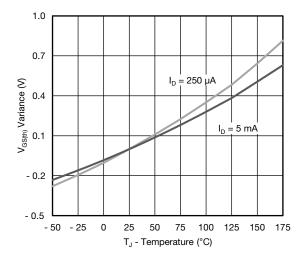
On-Resistance vs. Junction Temperature



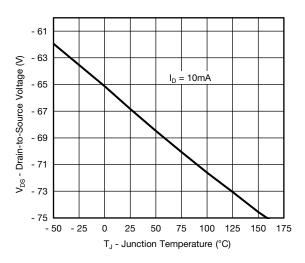
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

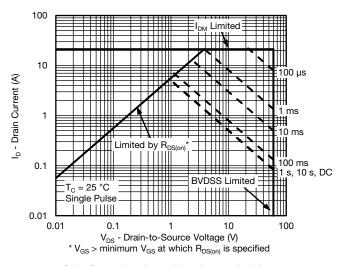


Threshold Voltage

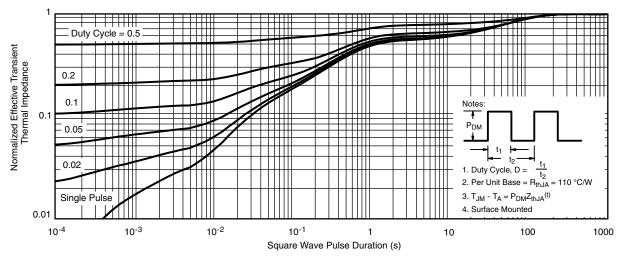


Drain-to-Source Voltage vs. Junction Temperature



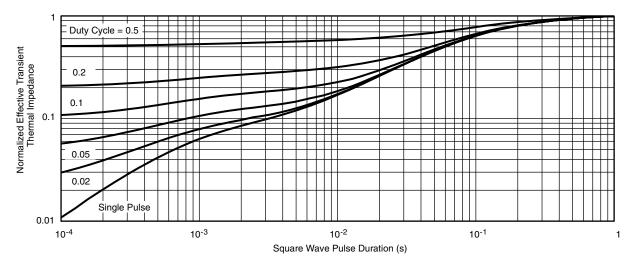


Safe Operating Area, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Ambient





Normalized Thermal Transient Impedance, Junction-to-Foot

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TSOP: 5/6-LEAD

JEDEC Part Number: MO-193C





5-LEAD TSOP







	MIL	LIMETER	RS	INCHES			
Dim	Min	Nom	Max	Min	Nom	Max	
Α	0.91	-	1.10	0.036	-	0.043	
A ₁	0.01	-	0.10	0.0004	-	0.004	
A ₂	0.90	-	1.00	0.035	0.038	0.039	
b	0.30	0.32	0.45	0.012	0.013	0.018	
С	0.10	0.15	0.20	0.004	0.006	0.008	
D	2.95	3.05	3.10	0.116	0.120	0.122	
E	2.70	2.85	2.98	0.106	0.112	0.117	
E ₁	1.55	1.65	1.70	0.061	0.065	0.067	
е		0.95 BSC		0.0374 BSC			
e ₁	1.80	1.90	2.00	0.071	0.075	0.079	
L	0.32	-	0.50	0.012	-	0.020	
L ₁		0.60 Ref		0.024 Ref			
L ₂		0.25 BSC 0.010 BSC					
R	0.10	-	-	0.004	-	-	
θ	0°	4°	8°	0°	4°	8°	
θ1		7° Nom			7° Nom		
ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540							

Document Number: 71200 18-Dec-06



Recommended Land Pattern For TSOP-5L / TSOP-6L



Note

• All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022 DWG: 3010



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